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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: KINNEY et al. Attorney Docket No.: UNTYP025
Application No.: 10/605,757 Examiner: not yet assigned
Filed: October 23, 2003 Group: 2818
Title: MULTI-LAYER CONDUCTIVE MEMORY DEVICE Confirmation No.: 2756

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the U.S. Postal Service with sufficient postage as first-class mail in an envelope addressed to the Commissioner for Patents, P.O. Box 1450 Alexandria, VA 22313-1450 on JUNE 16, 2004.

Signed: 
Sally Zumba

INFORMATION DISCLOSURE STATEMENT
37 CFR §§1.56 AND 1.97(b)

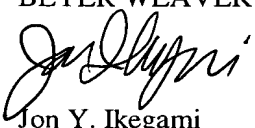
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Dear Sir/Ms.:

The references listed in the attached PTO Form 1449, copies of which are attached, may be material to examination of the above-identified patent application. Applicants submit these references in compliance with their duty of disclosure pursuant to 37 CFR §§1.56 and 1.97. The Examiner is requested to make these references of official record in this application.

This Information Disclosure Statement is not to be construed as a representation that a search has been made, that additional information material to the examination of this application does not exist, or that these references indeed constitute prior art.

This Information Disclosure Statement is: (i) filed within three (3) months of the filing date of the above-referenced application, (ii) believed to be filed before the mailing date of a first Office Action on the merits, or (iii) believed to be filed before the mailing of a first Office Action after the filing of a Request for Continued Examination under §1.114. Accordingly, it is believed that no fees are due in connection with the filing of this Information Disclosure Statement. However, if it is determined that any fees are due, the Commissioner is hereby authorized to charge such fees to Deposit Account 500388 (Order No. UNTYP025).

Respectfully submitted,
BEYER WEAVER & THOMAS, LLP

Jon Y. Ikegami
Registration No. 51,115

P.O. Box 778
Berkeley, CA 94704-0778
(650) 961-8300



Form 1449 (Modified)	Atty Docket No. UNTP025	Application No.: 10/605,757
Information Disclosure Statement By Applicant	Applicant: RINERSON et al.	
(Use Several Sheets if Necessary)	Filing Date 10/23/2003	Group 2818

U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
	A1	6,204,139	3/2001	Liu et al.			

Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation Yes	Translation No
	B1							

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
	C1	Beck et al., "Reproducible switching effect in thin oxide films for memory applications", 2000, Applied Physics Letters, Vol. 77, No. 1, pp. 139-141.
	C2	Betsuyaku et al., "Material Design for the Fabrication of <i>p</i> -type SrTiO ₃ ", 2001, Jpn. J. Appl. Phys., Vol. 40, pp. 6911-6912.
	C3	Gerstner et al., "Nonvolatile memory effects in nitrogen doped tetrahedral amorphous carbon thin films", 1998, Journal of Applied Physics, Vol. 84, No. 10, pp. 5647-5651.
	C4	Kim et al., "Leakage Current Properties of (Ba, Sr)TiO ₃ Films on Doped (Ba, Sr)RuO ₃ Electrodes", 2002, Journal of the Korean Physical Society, Vol. 41, No. 2, pp. 227-231.
	C5	Liu et al., "Electric-pulse-induced reversible resistance change effect in magnetoresistive films", 2000, Applied Physics Letters, Vol. 76, No. 19, pp. 2749-2571.
	C6	Simmons et al., "New conduction and reversible memory phenomena in thin insulating films", 1967, Proc. Roy. Soc. A., Vol. 301, pp. 77-102.
	C7	Waser, "Bulk Conductivity and Defect Chemistry of Acceptor-Doped Strontium Titanate in the Quenched State", 1991, J. Am. Ceram. Soc., Vol. 74, No. 8, pp. 1934-1940.
	C8	Waser, "dc Electrical Degradation of Perovskite-Type Titanates: I, Ceramics", 1990, J. Am. Ceram. Soc., Vol. 73, No. 6, pp. 1645-1653.
	C9	Watanabe et al., "Current-driven insulator-conductor transition and nonvolatile memory in chromium-doped SrTiO ₃ single crystals", 2001, Applied Physics Letters, Vol. 78, No. 23, pp. 3738-3740.
	C10	Watanabe, "Electrical transport through Pb(Zr, Ti)O ₃ <i>p-n</i> and <i>p-p</i> heterostructures modulated by bound charges at a ferroelectric surface: Ferroelectric <i>p-n</i> diode",
	C11	Watanabe et al., "Highly Resolved Conduction Properties of Ferroelectric/Semiconductor Diodes Exhibiting Memory Effect", 1998, Journal of the Korean Physical Society, Vol. 32, pp. S1361-S1364.
	C12	Zhuang et al., "Novell Colossal Magnetoresistive Thin Film Nonvolatile Resistance Random Access Memory (RAM)", © 2002 IEEE, 0-7803-7463-X/02
Examiner	Date Considered	

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.